

Device Modeling Report

COMPONENTS: Insulated Gate Bipolar Transistor (IGBT)
PART NUMBER: GT25Q101
MANUFACTURER: TOSHIBA

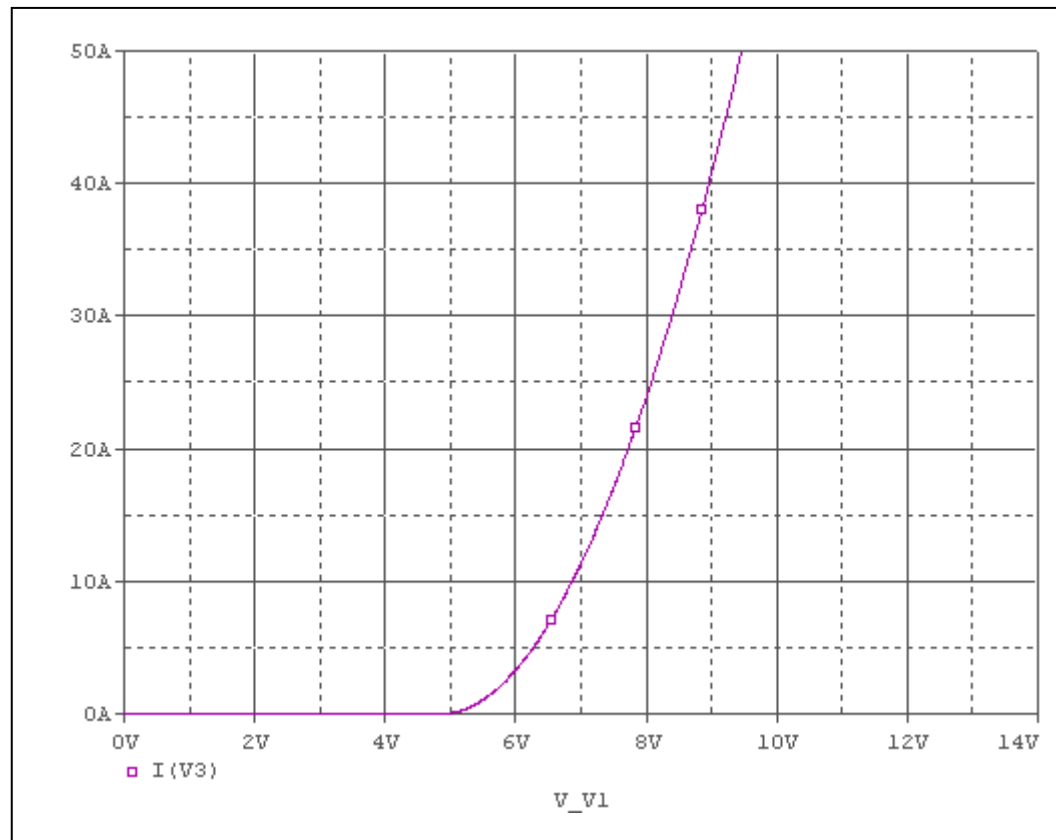


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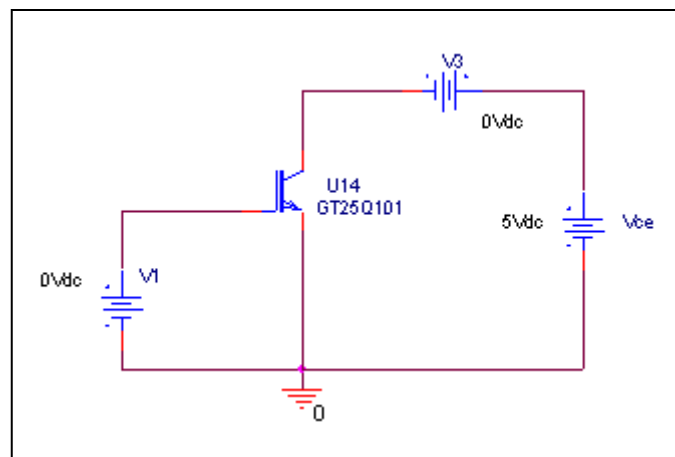
PSpice model parameter	Model description
TAU	Ambipolar Recombination Lifetime
KP	MOS Transconductance
AREA	Area of the Device
AGD	Gate-Drain Overlap Area
WB	Metallurgical Base Width
VT	Threshold Voltage
KF	Triode Region Factor
CGS	Gate-Source Capacitance per Unit Area
COXD	Gate-Drain Oxide Capacitance per Unit Area
VTD	Gate-Drain Overlap Depletion Threshold

Transfer Characteristics

Circuit Simulation result

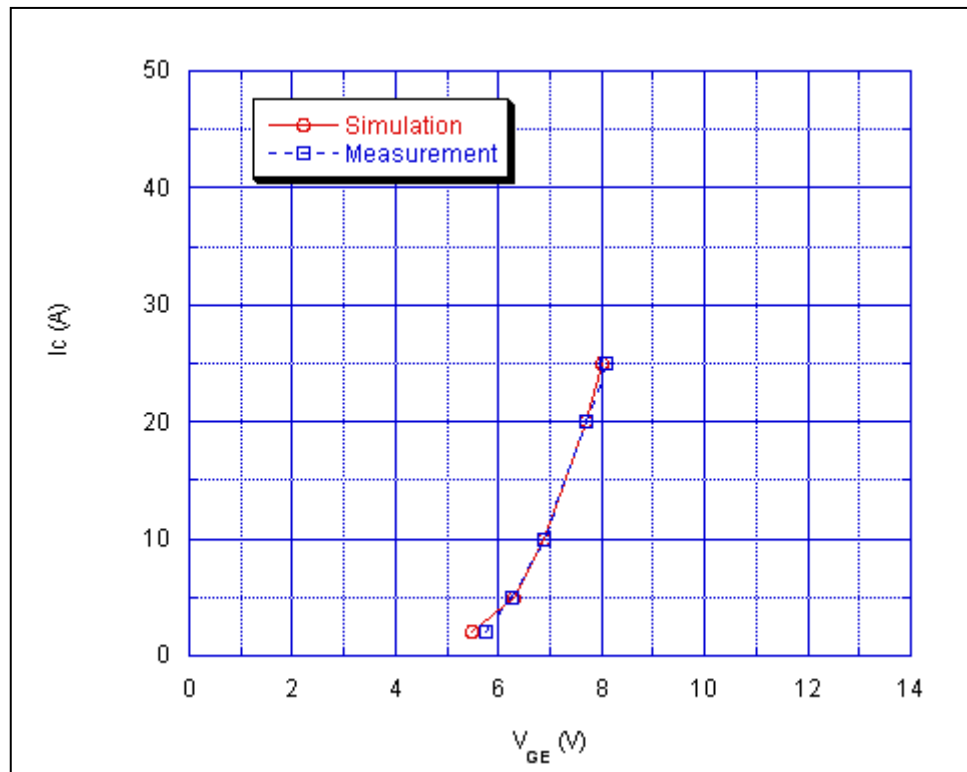


Evaluation circuit



Comparison Graph

Circuit Simulation Result



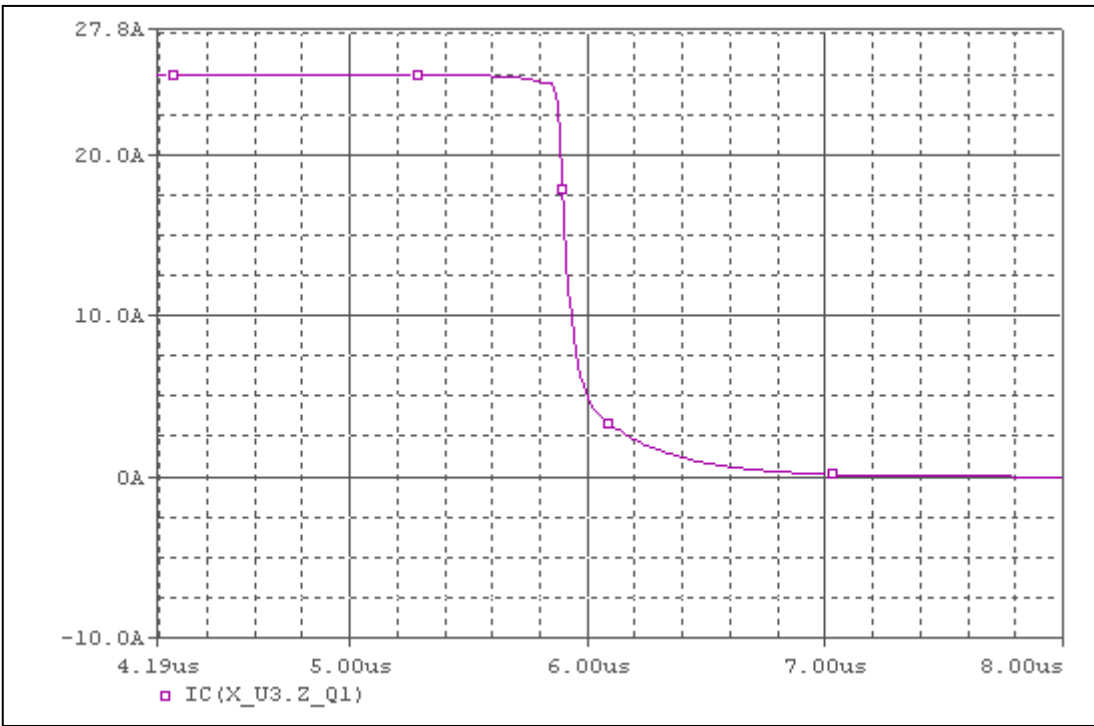
Simulation Result

Test condition : $V_{ce} = 5$ V

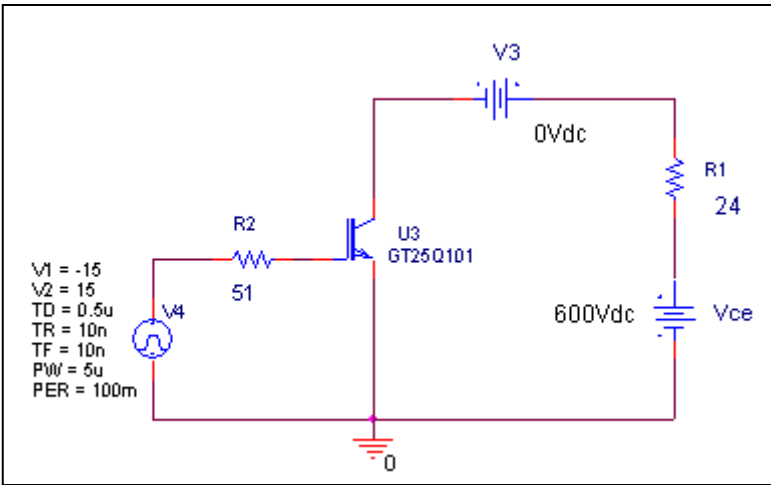
I_c (A)	V_{ge} (V)		Error (%)
	Measurement	Simulation	
2	5.5	5.7480	4.50909
5	6.3	6.2677	-0.51270
10	6.9	6.8661	-0.49130
20	7.7	7.7165	0.21429
25	8	8.0787	0.98375

Fall Time Characteristics

Circuit Simulation result



Evaluation circuit

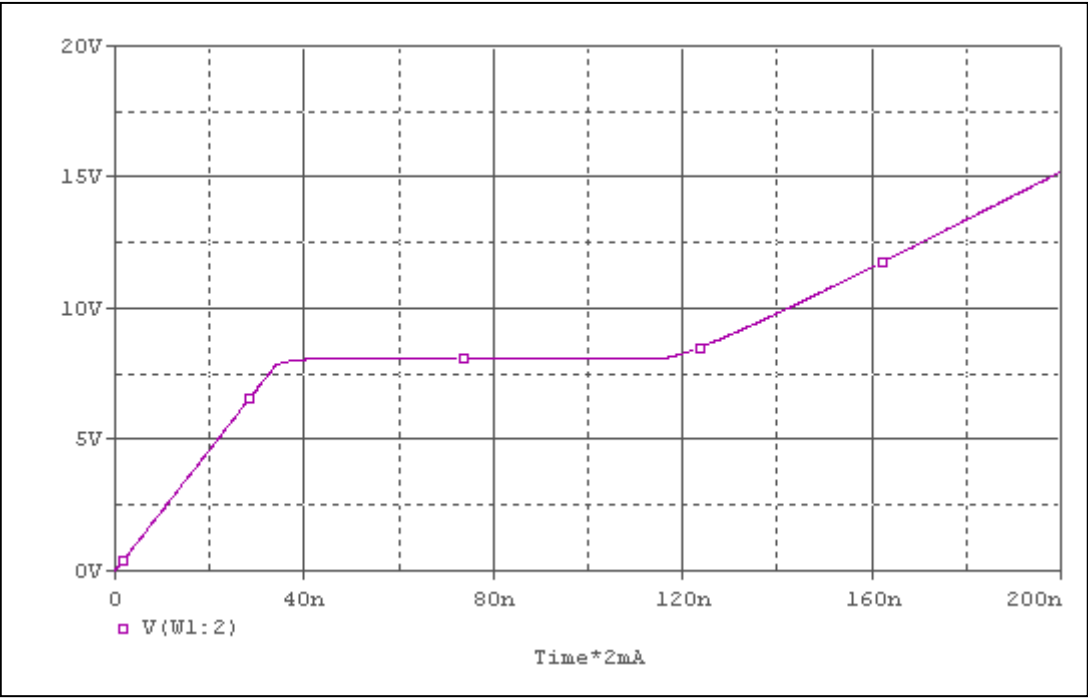


Test condition $I_c=25(A)$, $V_{ce}=600(V)$

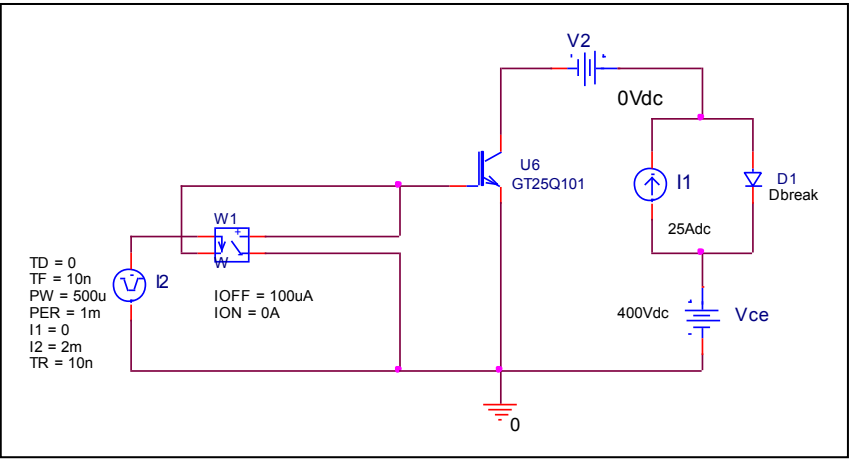
tf	Measurement		Simulation		Error
	0.3	us	0.301233	us	

Gate Charge Characteristics

Circuit Simulation result



Evaluation circuit

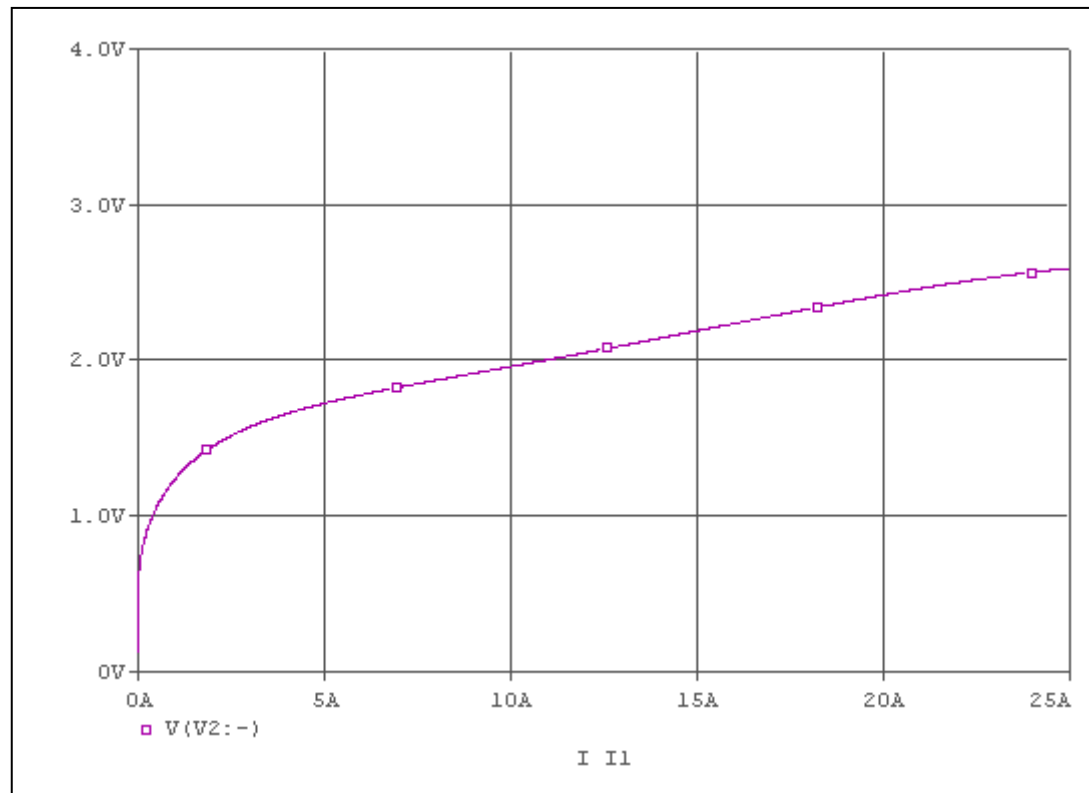


Test condition : Vce=400(V) ,Ic=25(A) ,Vge=12.5(V)

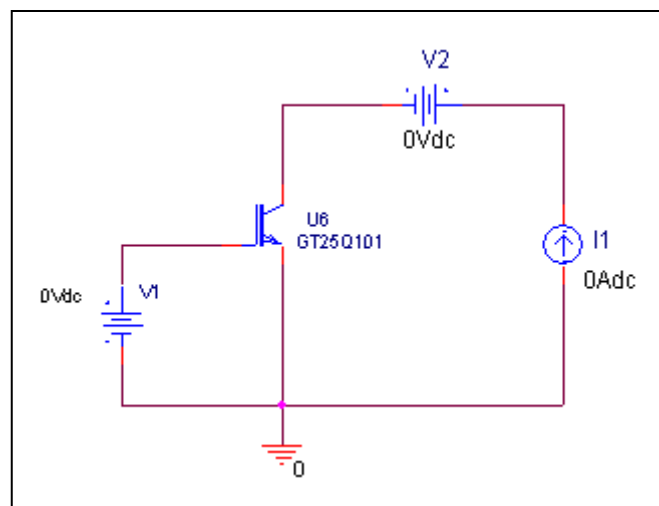
	Measurement		Simulation		Error(%)
Qge	34	nc	34.506	nc	1.48824
Qgc	82	nc	82.857	nc	1.04512
Qg	174	nc	170.550	nc	-1.98276

Saturation Characteristics

Circuit Simulation result

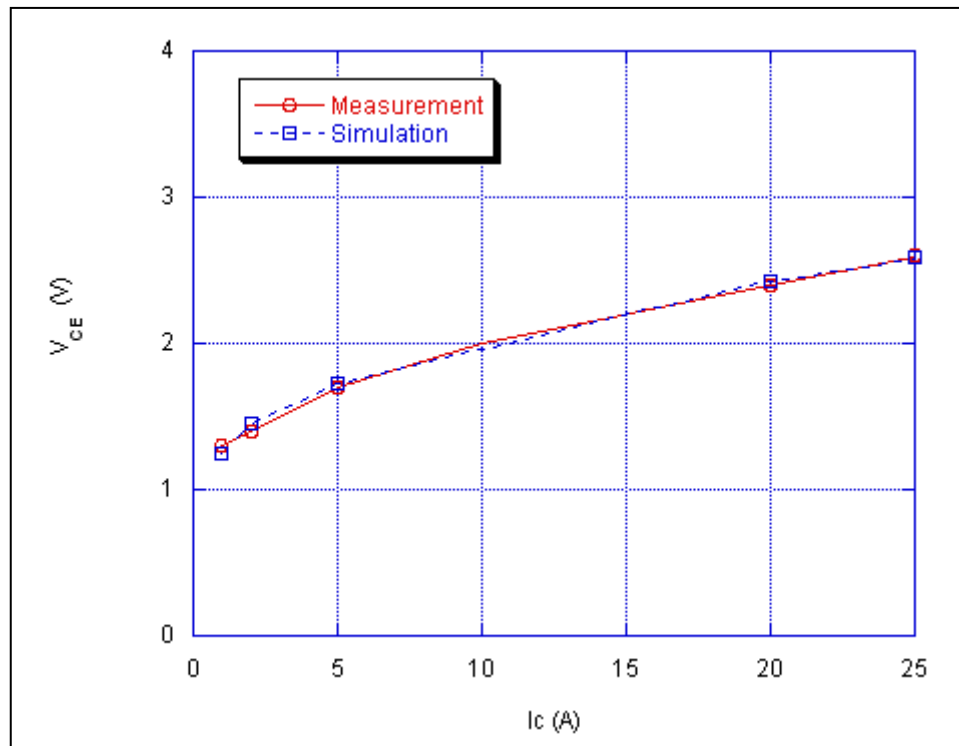


Evaluation circuit



Comparison Graph

Circuit Simulation Result



Simulation Result

Ic(A)	Vce(sat)(V)		Error (%)
	Measurement	Simulation	
1	1.3	1.2467	-4.10000
2	1.4	1.4488	3.48571
5	1.7	1.7247	1.45294
10	2	1.9604	-1.98000
20	2.4	2.4204	0.85000
25	2.6	2.5920	-0.30769